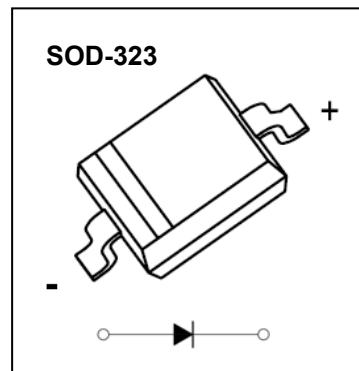


SOD-323 Plastic-Encapsulate Diodes**FEATURES**

For use in low voltage, high frequency inverters
Free wheeling, and polarity protection applications

MARKING:

B5817WS :SJ	B5818WS :SK	B5819WS :SL
- SJ +	- SK +	- SL +

**Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C**

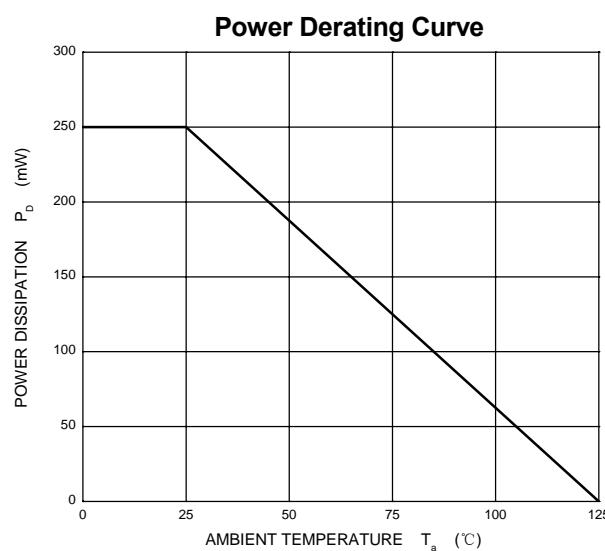
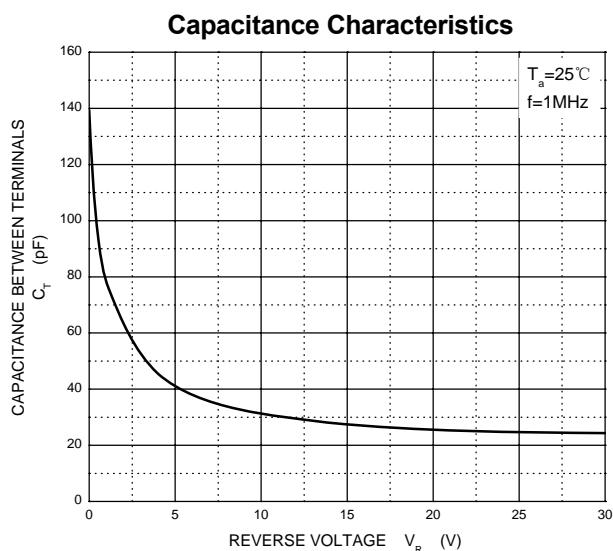
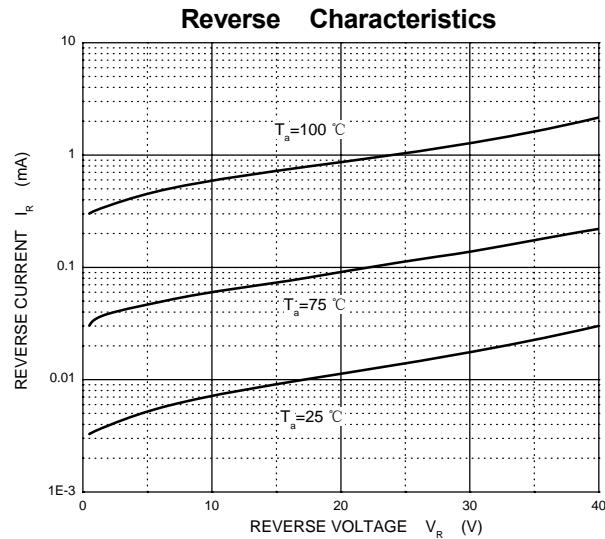
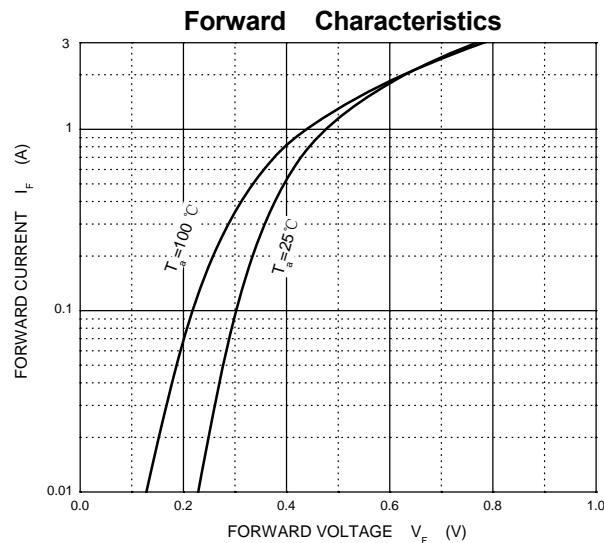
Parameter	Symbol	B5817WS	B5818WS	B5819WS	Unit
Non-repetitive peak reverse voltage	V _{RM}	20	30	40	V
Peak repetitive peak reverse voltage	V _{RRM}				
Working peak reverse voltage	V _{RWM}	20	30	40	V
DC blocking voltage	V _R				
RMS reverse voltage	V _{R(RMS)}	14	21	28	V
Average rectified output current	I _O		1		A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I _{FSM}		9		A
Repetitive peak forward current	I _{FRM}		1.5		A
Power dissipation	P _d		250		mW
Thermal resistance junction to ambient	R _{θJA}		400		°C/W
Junction temperature	T _J		125		°C
Storage temperature	T _{STG}		-55~+150		°C

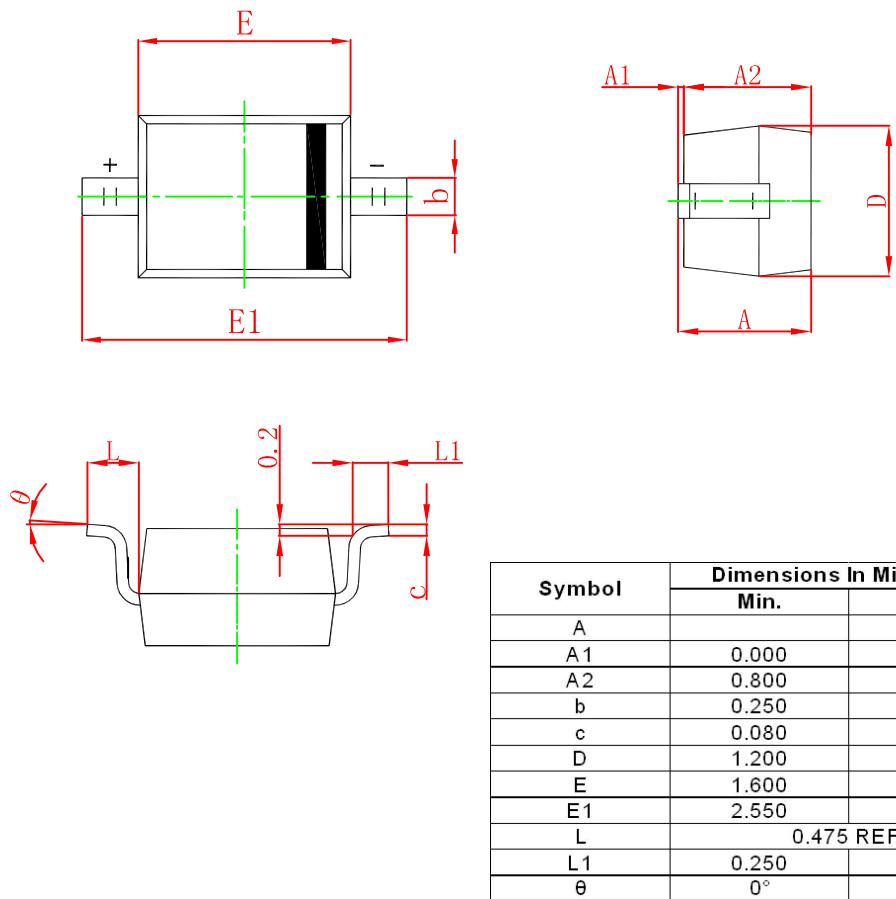
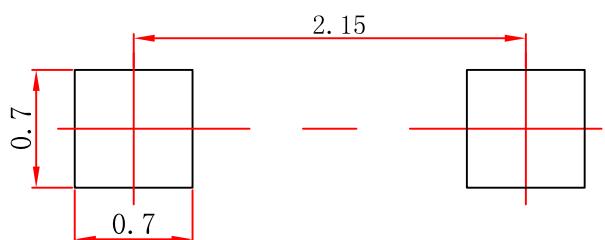
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R =1mA B5817WS B5818WS B5819WS	20 30 40		V
Reverse voltage leakage current	I _R	V _R =20V B5817WS V _R =30V B5818WS V _R =40V B5819WS		1	mA
Forward voltage	V _F	B5817WS I _F =1A I _F =3A B5818WS I _F =1A I _F =3A B5819WS I _F =1A I _F =3A		0.45 0.75 0.55 0.875 0.6 0.9	V
Diode capacitance	C _D	V _R =4V, f=1MHz		120	pF



Typical Characteristics



SOD-323 Package Outline Dimensions**SOD-323 Suggested Pad Layout****Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

